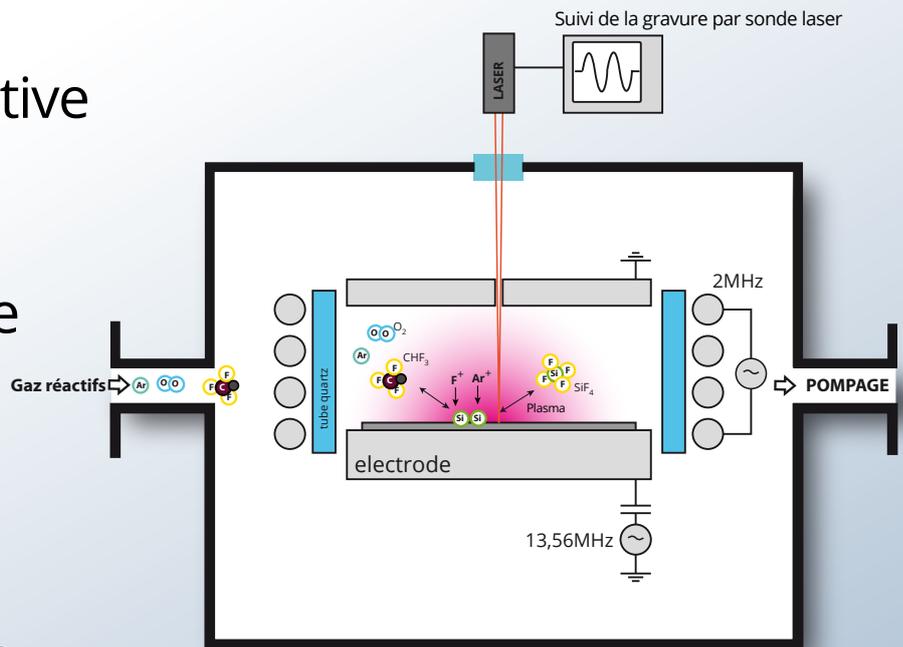


Gravure ICP RIE

Gravure ionique réactive

*Inductive Coupled Plasma
Reactive Ion Etching*

Technique de gravure sèche par plasma



→ Effet physique :

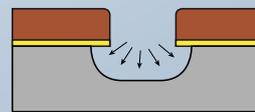
bombardement de gaz ionisés

→ Effet chimique :

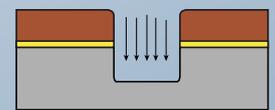
Gaz fluorés (gravure du Si)

Gaz chlorés (gravure des métaux et III-V)

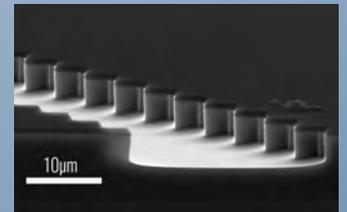
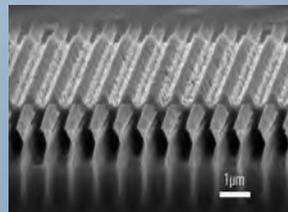
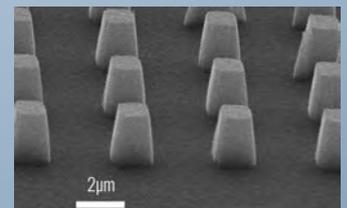
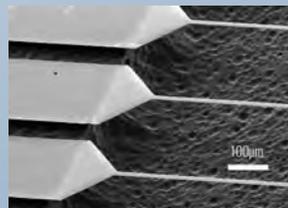
→ Contrôle de la gravure



isotrope



anisotrope



Equipements



ICP RIE Chlorée
Oxford plasmalab 100



ICP RIE fluorée
Corial 200 IL



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